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Toshiba UFS Memory Overview for LGMC

in Seoul, Korea Oct. 22nd 2015

Memory Application Engineering Dept. I
Memory Division
Semiconductor & Storage Products Company
Toshiba Corporation

e-MMCTM is a trademark and a product category for a class of embedded memory products built to the joint JEDEC/MultiMediaCard Association (MMCA) MMC Standard specification.

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Agenda

- Comparison : UFS vs. e-MMC
- > UFS Specific feature : UME (Unified Memory Extension)
- > Toshiba UFS latest roadmap







Toshiba's Current Portfolio

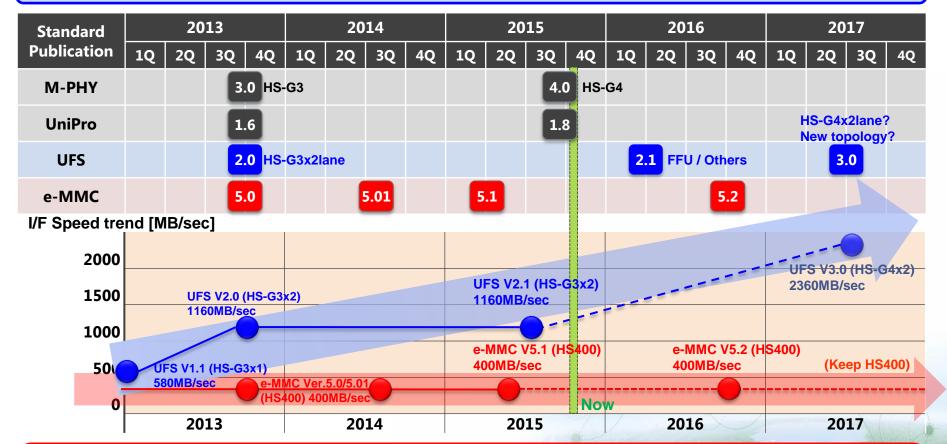
e-MMC is a DeFact Standard Memory for Mobile Applications such as Smartphone and Tablet. UFS is a successor of e-MMC.

1Gb 2Gb 4Gb 1GB 2GB 4GB 8GB **16GB 32GB** 256GB **64GB 128GB SLC NAND TSOP** 63FBGA 132BGA **BENAND** NAND I/F 63FBGA **Embedded type** on die ECC engine **TSOP Smart NAND** Controller embedded / pseudo SLC partition supporte **TSOP 153FBGA** e-MMC **HS-MMC I/F** (169FBGA) Controller embedded / pseudo SLC partition supported 153FBGA **UFS UFS I/F** (169FBGA) Controller embedded / pseudo SLC partition suppo Next Gen. **BGA** type or ... I/F **SSD** Removable type SATA I/F Controller embedded SD Card / microSD Card SD I/F Controller embedded **USB Memory** 64GB TOSHIBA **USB I/F** Controller embedded



JEDEC / MIPI standardization schedule

Toshiba has essential IP's (M-PHY, UniPro, NAND, Controller) for UFS development. We will expand and lead UFS memory market with these.



Toshiba's strategy

e-MMC : Keep supporting the customers, but no huge investment anymore.

UFS: Focusing on UFS development and following JEDEC standard and market.



New feature list for each standard ver.

Toshiba has essential IP's (M-PHY, UniPro, NAND, Controller) for UFS development. And move the development resource to UFS step-by-step.

| | e-MMC | | | | | | | | | | |
|--|---|---|--|--|--|--|--|--|--|--|--|
| Ver. | 5.0/5.01 | 5.1 | 5.2 | | | | | | | | |
| Standard | JESD84-B50 / 50.1 | JESD84-B51 | tbd | | | | | | | | |
| Publication | Sep.'13 / Jul.'14 (Done) | Feb.'15 | 3Q'16(Not fixed yet) | | | | | | | | |
| Main New feature on consensus list | HS400 & Adding DS pin Product State Awareness Device Health Report Field FW update etc. | Command Queuing (Optional) Cache barrier RPMB Throughput Improvement(8KB) Enhanced Strobe at HS400 etc. | tbd Companies don't like to introduce the items which causes HW changes. | | | | | | | | |
| Main Proposal Under discussion | n/a | No other Proposal (Fixed in Dec.'14 Committee meeting) | I/F improvement(HS533/HS667) Inline encryption(HCI) CQ improvement(HCI) HS400 tuning | | | | | | | | |

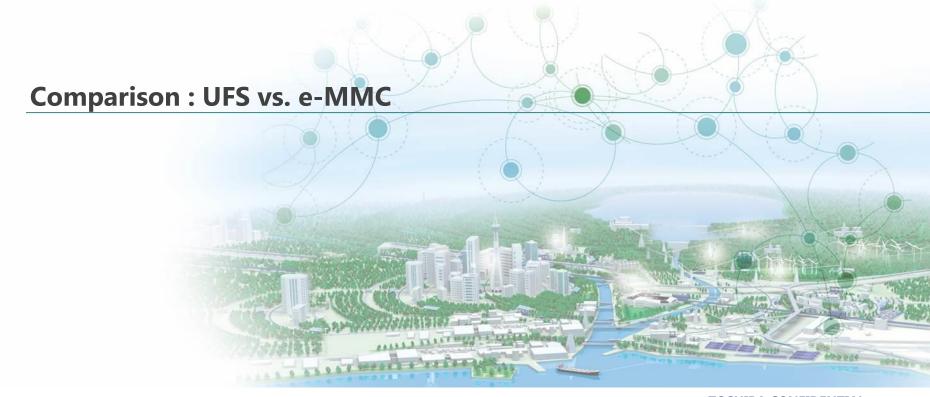
| | | UFS | | | | | | |
|--|---|---|--|---|--|--|--|--|
| Ver. | 1.0/1.1 | 2.0 | 2.1 | х.х | | | | |
| Stdndard JESD220 / 220A | | JESD220B | tbd | tbd | | | | |
| Publication | Feb.'11 / Jun.'12 (done) | Sep.'13 (done) | Mar.'16(tbd) | Sep'17(tbd) | | | | |
| Main New feature on consensus list | Initial ver. HS-G2 Single-lane support M-PHY2.0 / UniPro1.41 | HS-G3 support Multi-lane support M-PHY3.0 / UniPro1.6 Power-Up/down sequence etc. | Editorial change Minor change | UFS Lite - Remove LCC feature - Remove PWM-G2-4 - Relax the timing, etc, UFS Card | | | | |
| Main Proposal Under discussion | n/a | n/a | Inline encryption(HCI) Multiple LU(8->32) etc. | HS-G4Bx2 New topology etc. | | | | |



Memory I/F Trend on Mobile Application * Toshiba estimation TOSHIBA

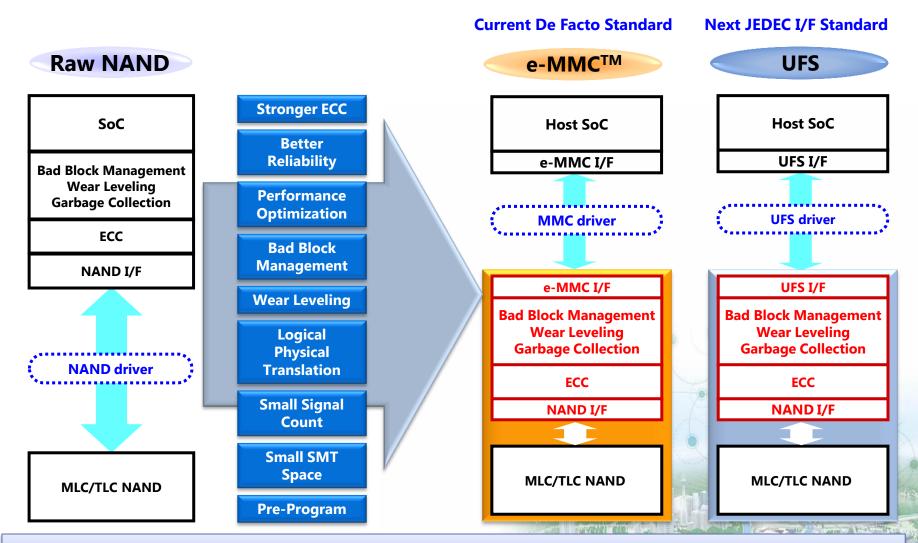
UFS memory will be applied to High-tier smartphone in 2015. After that in Mid/Low-tier area, UFS will replace e-MMC memory step-by-step in 2016 or later.

| Application | os | Mem | ory | 2015 | 2016 | 2017 | | |
|-------------------------|--------------------|-----------|---------|-------------------------|-------------------------|-------------------|--|--|
| High-tier Smartphone | Android Windows | | I/F | e-MMC V5.1 | V5.1 | V5.x | | |
| Smartphone | BlackBerry | Storage | | UFS V2.0 | V2.0/2.1 | V2.1 | | |
| | | | Density | 16GB-128GB | 32GB-128GB | 64GB-256GB | | |
| | Remov | | Card | SD2.0 / 3.0 / 4.0 (UHS) | SD2.0 / 3.0 / 4.0 (UHS) | SD3.0 / 4.0 (UHS) | | |
| | | DRAM | | LPDDR3 / LPDDR4 | LPDDR3 / LPDDR4 | LPDDR4 | | |
| Mid-tier Smartphone | Android Windows | | I/F | e-MMC V5.1 | V5.1 | V5.x | | |
| | BlackBerry | Storage | | UFS | V2.0/2.1 | V2.1 | | |
| | | | Density | 8GB-32GB | 16GB-64GB | 32GB-128GB | | |
| | | Removable | Card | SD2.0 / 3.0 / 4.0 (UHS) | SD2.0 / 3.0 / 4.0 (UHS) | SD3.0 / 4.0 (UHS) | | |
| | | DRAM | | LPDDR3 / LPDDR4 | LPDDR3 / LPDDR4 | LPDDR4 | | |
| Low-tier smartphone | Android Windows | C: | I/F | e-MMC V5.0/5.1 | V5.1 | V5.x | | |
| | BlackBerry | Storage | | UFS | | V2.1 | | |
| | | | Density | 4-16GB | 8-32GB | 16GB-64GB | | |
| | | Removable | Card | SD2.0 / 3.0 / 4.0 (UHS) | SD2.0 / 3.0 / 4.0 (UHS) | SD3.0 / 4.0 (UHS) | | |
| | | DRAM | | LPDDR3 | LPDDR3 | LPDDR3/LPDDR4 | | |
| 2-in-1 PC Tablet | Android Windows | | | e-MMC V5.1 | V5.1 | V5.x | | |
| lablet | windows | Storage | I/F | UFS | V2.0/2.1 | V2.1 | | |
| | | | Density | 16-128GB | 32-256GB | 64GB-256GB | | |
| | | Removable | Card | SD2.0 / 3.0 / 4.0 (UHS) | SD2.0 / 3.0 / 4.0 (UHS) | SD3.0 / 4.0 (UHS) | | |
| | | DRAM | | LPDDR3 / LPDDR4 | LPDDR4 / DDR4? | LPDDR4 / DDR4? | | |





Comparison: UFS vs. e-MMC(1)



Embedded controller solution can provide better Raw NAND Management.



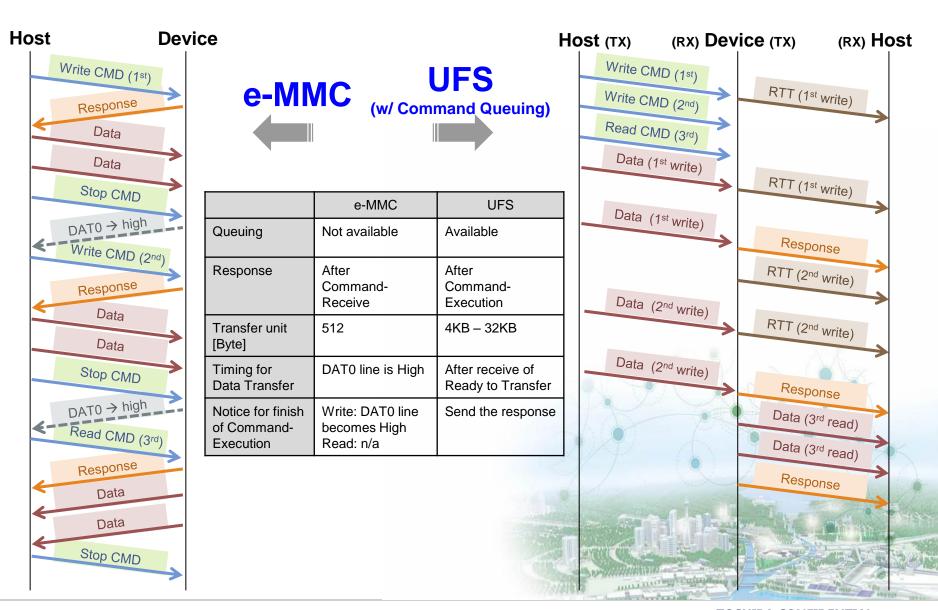
Comparison: UFS vs. e-MMC(2)

e-MMC features Parallel I/F which has a restriction for further performance improvement beyond HS400(400bps). Meanwhile, UFS features high-speed serial I/F which maintains a performance scalability to extend in the future.

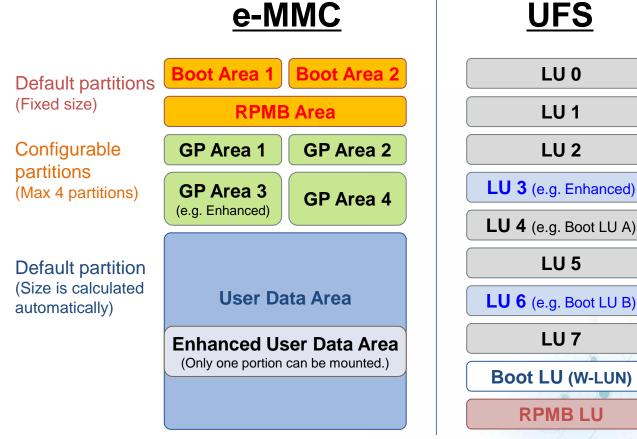
| | | e-MMC | UFS | | | | | | |
|---------------|--------------|--|--|--|--|--|--|--|--|
| | Year | Since 2007 | Market adoption started in 2015 | | | | | | |
| 1.75 | Architecture | MMC I/F (Bus, Parallel I/F) Host e-MMC | UFS I/F (Serial I/F) Tx Host UFS | | | | | | |
| I/F | Speed | 400Mbps (=400MB/s, Ver.5.0) *Restricted for further improvement | 5.8Gbps x 2 Lanes (=1160MB/s, Ver.2.0) | | | | | | |
| | Pin count | 11 (8 I/O and 3 control) | 6 (4 I/O and 2 control) or 10 (in case of 2 lanes) | | | | | | |
| | Signal amp. | 1.8V or 1.2V | 400mVp-p | | | | | | |
| | Duplex | Half (In serial to send and/or receive the data) | Full (Simultaneously to send and receive the data.) | | | | | | |
| Command Queue | | Supported from Ver.5.1 | Support | | | | | | |
| Co | ommand Set | ММС | SCSI | | | | | | |

The state of the s

Comparison: UFS vs. e-MMC(3) Data transfer



Comparison: UFS vs. e-MMC(4) LU/Partition



LU 6 (e.g. Boot LU B) Well-known LU **Boot LU (W-LUN)** (Boot LU A or B is mapped) **RPMB LU** Well-known LU (Fixed size)

*Each configurable partition and LU can be set as enhanced memory

September 19 19 19

Configurable LUs

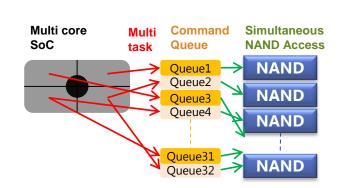
(Max 8 Logical Units: Max 2

LUs can be set as Boot LU)

Comparison: UFS vs. e-MMC(5) Protocol-1

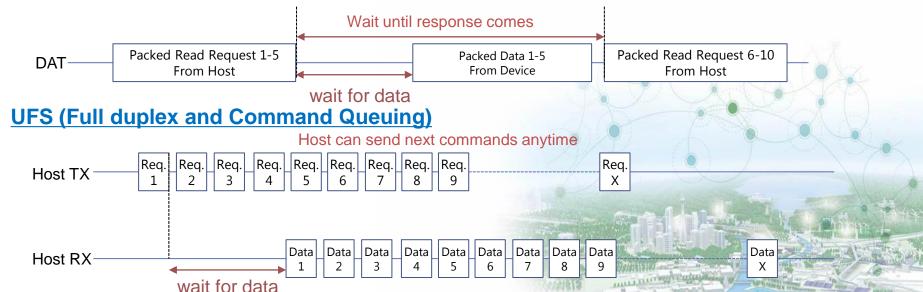
Multi task on UFS memory

UFS can make the difference on Multi Task access from the host.



| Sc | С | UFS | e-MMC | | | |
|---|---------------------------------------|---|---|--|--|--|
| Multi Core SoC & Issue multiple command | | Multi task will be executed in parallel. | Handled by sequential. | | | |
| Command(CMD) Queue | Add Task No./ID to each command | Task reorder will be implemented. | There are only simple rule for Task reorder. | | | |
| Simultaneous NAND Access | Reduce idle time on SoC side | Intelligent memory controller can simultaneously access to each NAND Flash. | Access will sequentially happen to each NAND Flash. | | | |

eMMC (Half duplex and Packed CMD)



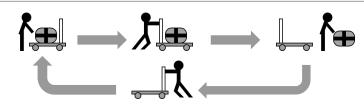


Comparison: UFS vs. e-MMC(6) Protocol-2

e-MMC (Legacy)

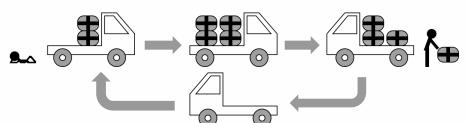
: Push-car type

- > Luggage have to be carried one by one.
- > 2nd luggage cannot be carried until push car comes back.



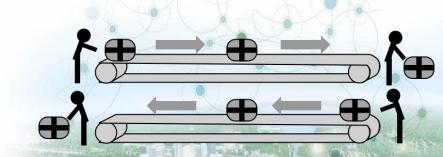
e-MMC (Packed Command): Truck type

- Many luggage can be delivered at once.
- Efficiency is not so good.
- > Only same kind of luggage can be delivered.
- > 2nd batch cannot be carried until truck returns.

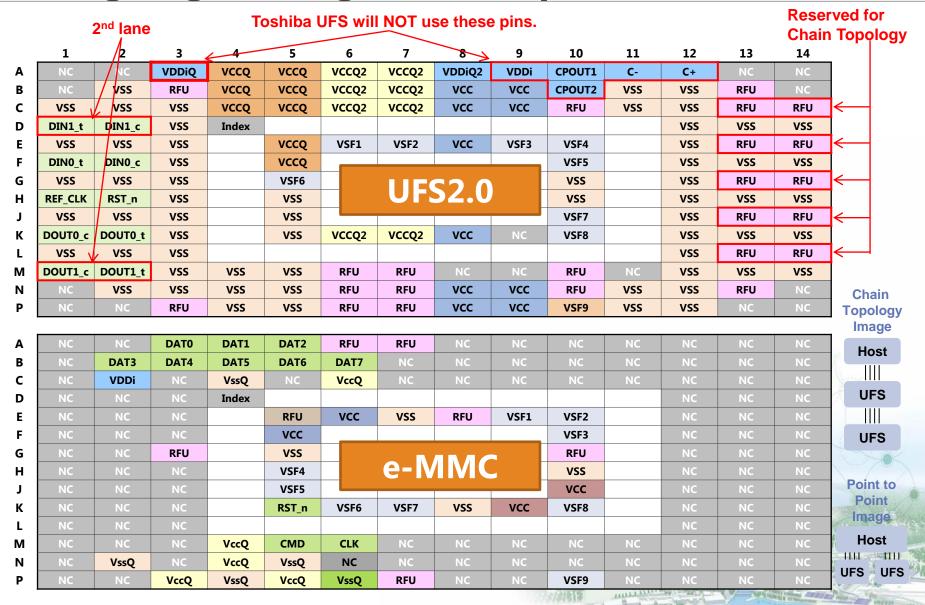


UFS (Command Queuing): Belt-conveyor type

- Many luggage can be delivered at once.
- Operator just can put on the belt.
- There are 2 belts (i.e. Receiver and Transfer lane)
 (Only 1 belt can be used in the case of e-MMC.)
- Many operators can simultaneously work (i.e. Multi Task)



Package signal assignment (Top view)





Toshiba Gen.3 UFS2.0 pin out & debugging pin

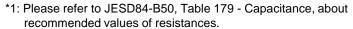
| _ | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 | 11 | 12 | 13 | 14 |
|-----|-------------|-------------|-------|-------|------|-------|---------------|------------------|------|--------|-----|-----|-----|-----|
| A | NC | NC | VDDiQ | vccq | vccq | VCCQ2 | VCCQ2 | VDDiQ2 | VDDi | CPOUT1 | C- | C+ | NC | NC |
| В | NC | VSS | RFU | vccQ | vccq | VCCQ2 | VCCQ2 | vcc | vcc | CPOUT2 | VSS | VSS | RFU | NC |
| С | vss | vss | VSS | vccq | vccq | VCCQ2 | VCCQ2 | vcc | vcc | RFU | VSS | vss | RFU | RFU |
| D | DIN1 _t | DIN1 _c | VSS | Index | | | | | | | | vss | vss | VSS |
| E | VSS | VSS | VSS | | vccq | VSF1 | VSF2 | vcc | VSF3 | VSF4 | | vss | RFU | RFU |
| F | DIN0 _t | DIN0 _c | VSS | | vccq | | | | | VSF5 | | vss | vss | VSS |
| G | vss | vss | vss | | VSF6 | | Debug S 8p | ignal pin oin | | vss | | VSS | RFU | RFU |
| н | REF _CLK | RST _n | vss | | vss | | | /i | | vss | | VSS | vss | vss |
| J | vss | vss | vss | | vss | | op v | /iew | | VSF7 | | vss | RFU | RFU |
| К | DOUT0 _c | DOUT0 _t | vss | | vss | VCCQ2 | VCCQ2 | vcc | NC | VSF8 | | vss | vss | vss |
| L | vss | vss | vss | | | | | | | | | vss | RFU | RFU |
| М | DOUT1 _c | DOUT1 _t | VSS | VSS | vss | RFU | RFU | NC | NC | RFU | NC | vss | vss | vss |
| N | NC | vss | vss | vss | vss | RFU | RFU | vcc | vcc | RFU | vss | vss | RFU | NC |
| . Р | NC | NC | RFU | VSS | vss | RFU | RFU | vcc | vcc | VSF9 | VSS | VSS | NC | NC |

Toshiba Gen.4 UFS2.0 pin out & debugging pin

| _ | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 | 11 | 12 | 13 | 14 |
|-----|-------------|-------------|-------|-------|------|-------|---------------|------------------|------|--------|-----|-----|-----|-----|
| Α | NC | NC | VDDiQ | vccq | vccQ | VCCQ2 | VCCQ2 | VDDiQ2 | VDDi | CPOUT1 | C- | C+ | NC | NC |
| В | NC | vss | RFU | vccq | vccQ | VCCQ2 | VCCQ2 | vcc | vcc | CPOUT2 | vss | VSS | RFU | NC |
| С | vss | vss | vss | vccq | vccq | VCCQ2 | VCCQ2 | vcc | vcc | RFU | vss | vss | RFU | RFU |
| D | DIN1 _t | DIN1 _c | vss | Index | | | | | | | | vss | vss | vss |
| E | vss | vss | vss | | vccq | VSF1 | VSF2 | vcc | VSF3 | VSF4 | | vss | RFU | RFU |
| F | DIN0 _t | DIN0 _c | vss | | vccq | | | | | VSF5 | | vss | vss | vss |
| G | vss | vss | vss | | VSF6 | | Debug S 2p | ignal pin pin | | vss | | vss | RFU | RFU |
| н | REF _CLK | RST _n | vss | | VSS | | | li ou | | vss | | VSS | vss | vss |
| J | vss | vss | vss | | VSS | | op \ | riew | | VSF7 | | VSS | RFU | RFU |
| К | DOUT0 _c | DOUT0 _t | vss | | vss | VCCQ2 | VCCQ2 | vcc | NC | VSF8 | | vss | vss | vss |
| L | vss | vss | vss | | | | | | | | | vss | RFU | RFU |
| М | DOUT1 _c | DOUT1 _t | vss | vss | vss | RFU | RFU | NC | NC | RFU | NC | vss | vss | vss |
| N | NC | vss | vss | VSS | VSS | RFU | RFU | vcc | vcc | RFU | vss | VSS | RFU | NC |
| . Р | NC | NC | RFU | VSS | VSS | RFU | RFU | vcc | vcc | VSF9 | vss | VSS | NC | NC |

Recommended System Design

e-MMC 1.8/3.3V SoC e-MMC T R_{RST} RST n *2 200MHz (HS400) CLK $R_{\underline{CMD}}$ **CMD** R_{DAT} **DAT0** *1 ${\color{red}\overline{\bf 1}}\, R_{\rm DAT}$ DAT7 *1 DS *3 R_{DS} **PMIC** 3.3V VCC 1.8V/3.3V **VCCQ VDDiQ** VSS/VSSQ Unused pins treatment



RFU

NC

UFS 1.2V R_{RST} SoC **UFS** RST n RST n* 19.2M/26M/38.4M/52MHz 1.2V amplitude **REF CLK*** REF_CLI is required. **Default setting** Differential signal pair (Isometric wiring) DOUT0/1 t *1 DOUT0/1 c *1 4pin for 1lane Differential signal pair 8pin for 2lane (Isometric wiring) DIN0/1 t *1 DIN0/1 c *1 **PMIC** VCC 3.3V 1.8V VCCQ2 **VCCQ** 1.2V VDDiQ2 VSS Unused pins treatment VDDi NC VSFn/RFU NC(=Floating)

C+/C-

CPOUT1/2

VDDiO

NC

NC

NC or GND

NC or GND

NC

NC or GND

NC or GND

^{*2:} RST_n might be NC or connected to GND when it is not used. DAT4 - DAT7 should be NC in 4 bit mode.

^{*3:} DS should be left floating in case of not using HS400.

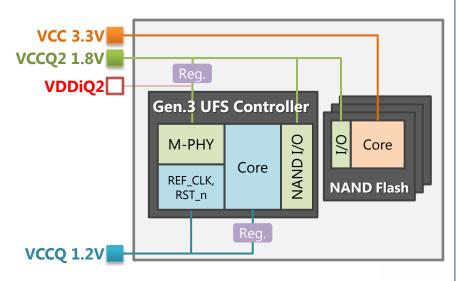
^{*1:} If some of DINn_t/c or DOUTn_t/c are not used, the DINn_t/c is recommended to be connected to GND and DOUTn_t/c is recommended to be left floating.

^{*2 :} Optional feature. Some host would like not to use it because Power-on write protection will be released with this.

^{*3 :} Mandate feature. REF_CLK shall always be required when the device is in HS-mode.

Block diagram : Toshiba 15nm UFS

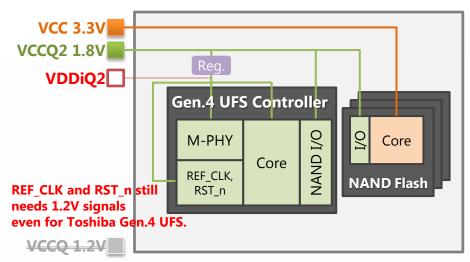
Toshiba "Gen.3" UFS Ver.2.0, 3 power rail



| Pin name | VDDiQ2 |
|----------|--------|
| Apply to | M-PHY |
| Typical | 2.2uF |
| min. | 0.7uF |
| max. | 2.4uF |

| PMIC for | Required Max. current |
|--------------|--------------------------|
| VCC (3.3V) | 750mA |
| VCCQ2 (1.8V) | 450mA |
| VCCQ (1.2V) | 450mA |

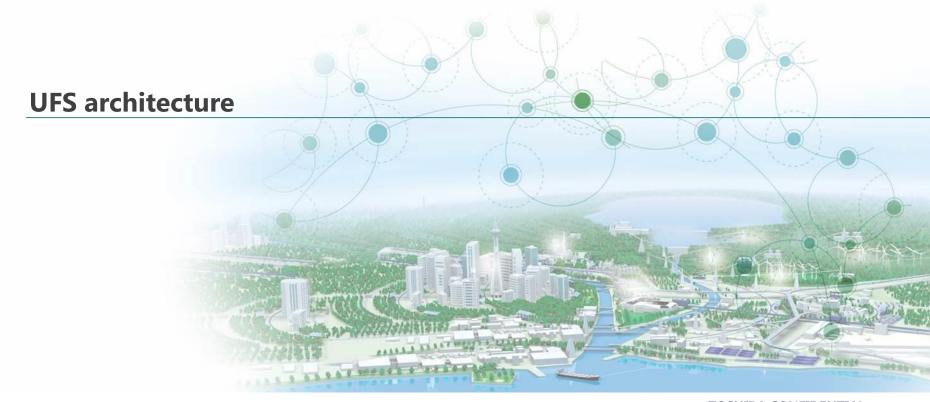
Toshiba "Gen.4" UFS Ver.2.0, 2 power rail



| Pin name | VDDiQ2 |
|----------|--------|
| Apply to | M-PHY |
| Typical | 2.2uF |
| min. | 0.7uF |
| max. | 2.4uF |

| PMIC for | Required Max. current |
|--------------|--------------------------|
| VCC (3.3V) | 600mA |
| VCCQ2 (1.8V) | 700mA |
| VCCQ (1.2V) | N/A |

Please prepare the suitable VDDiQ2(Cap.) and LDO (PMIC) accordingly





UFS protocol layer structure

UFS adopts protocol stack architecture like OSI reference model

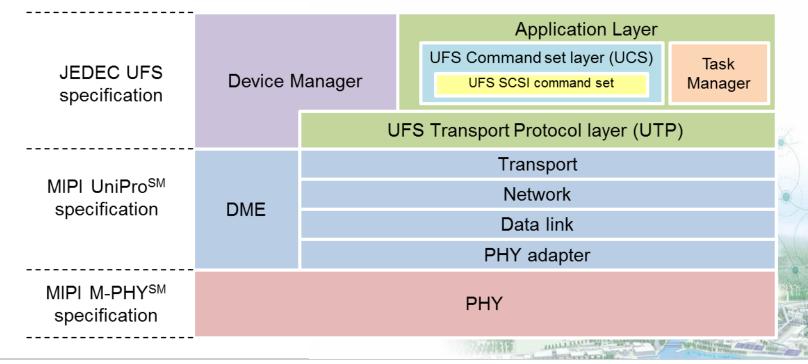
- Layer 1: M-PHYSM, which is defined by MIPI
- Layer 1.5-4: UniProSM, which is defined by MIPI
- Layer 5-7: UFS, which is defined by JEDEC

UFS specification defines 3 command types

Basic command (SCSI only in v2.0): Handled by UCS (Read/Write, etc.)

Task Management Request: Handled by Task Manager (abort/cancel task, etc.)

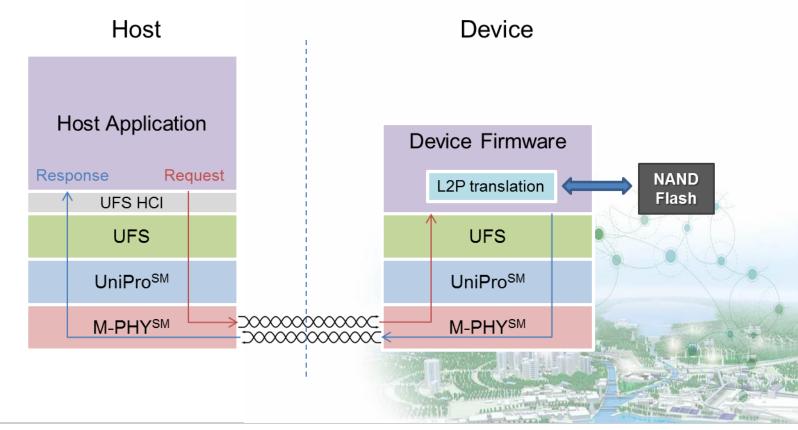
Query Request: Handled by Device Manager (access to descriptor, etc.)





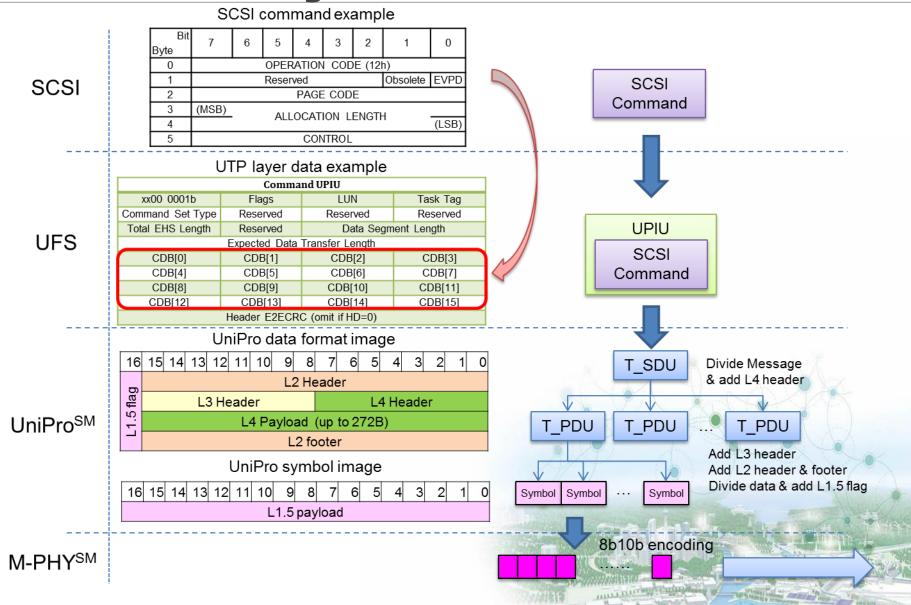
Host/Device Connection image

- Both host and device have same protocol stack under UFS layer
- Host application accesses to device through UFS Host Controller Interface (UFS HCI)
 - UFS HCI is also standardized by JEDEC





UFS data flow image in host controller

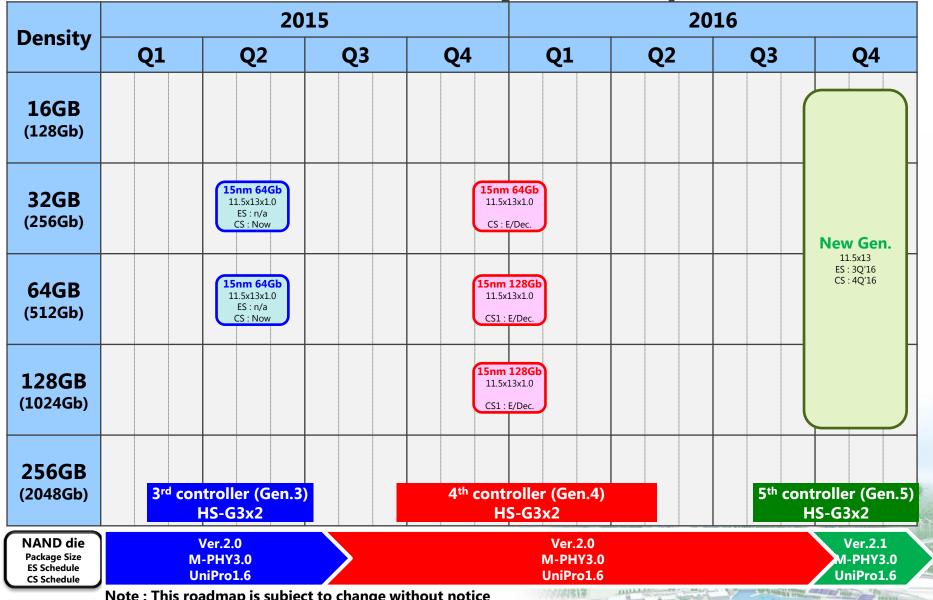








Toshiba UFS Ver.2.0 memory roadmap



Note: This roadmap is subject to change without notice



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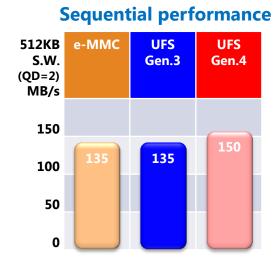
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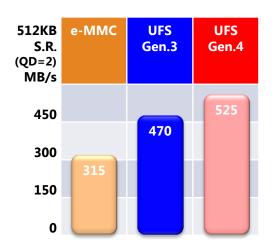
Toshiba UFS Performance data

This data is subject to change without notice.

| | | | | | | | | | | IIIS date | i is subj | ject to t | manige | withou | i ilotice. | |
|---------------------------|-------------|-----------------|------------------|--------|-----------|--------|-----------------|----------|-------------|-----------|---|-----------|--|--------|------------|--|
| UFS Ver. | | | | | | | Ver | ·.2.0 | | | | Ver.2. | 0(2.1) | | | |
| Power mode | | | | | | | | | | HS- | G3B | | | | | |
| Controller Gener | ation | | | | | | Ge | n.3 | | | | Ge | n.4 | | | |
| NAND Chip | | | | | | | 15nm | 64Gb | | 15nm | 64Gb | | 15nm | 128Gb | ib | |
| Density & Interle | eave | | | | | 32GB (| (4-Int.) | 64GB (| (8-Int.) | 32GB (| (4-Int.) | 64GB | (4-Int.) | 128GB | (4-Int.) | |
| Package (BGA) | Note | | | | | | L3x1.0 | | 13x1.2 | | <u>, , , , , , , , , , , , , , , , , , , </u> | 11.5x1 | <u> </u> | | , , | |
| CS schedule | | | | | | No | | | ow | 12 | 2/E | | 2/E | 11/E | (CSO) | |
| # of lane | | | | | | 1 | 2 | 1 | 2 | 1 | 2 | 1 | 2 | 1 | 2 | |
| # Of faile | | | | Poad | | 470 | 520 | 470 | 520 | 525 | 610 | 525 | 610 | 525 | 610 | |
| | | | 512KB chunk | | Normal | 135 | 135 | 165 | 170 | 153 | 153 | 153 | 153 | 153 | 153 | |
| | Seguential | OD:2 | JIZKO CHUHK | Write | Enhanced | 180 | 180 | 180 | 180 | 285 | 285 | 285 | 285 | 285 | 285 | |
| | | | | Read | | 440 | 480 | 440 | 480 | 520 | 610 | 520 | 610 | 520 | 610 | |
| Performance | | | 256KB chunk | | Normal | 90 | 100 | 110 | 120 | 150 | 150 | 150 | 150 | 150 | 150 | |
| | | | - CHAIR | Write | Enhanced | 150 | 160 | 150 | 160 | 285 | 285 | 285 | 285 | 285 | 285 | |
| Ra | D d | | | Read | | 23K | 23K | 30K | 30K | 25K | 25K | 25K | 25K | 25K | 25K | |
| | | QD:8 | 4KB chunk | \ | Cache-on | 7.0K | 7.0K | 7.2K | 7.2K | 15K | 15K | 15K | 15K | 15K | 15K | |
| | [IOps] | | | vvrite | Cache-off | 4.0K | 4.0K | 4.0K | 4.0K | 2.3K | 2.3K | 2.3K | 2.3K | 2.3K | 2.3K | |
| A | | | | | | 165 | 180 | 155 | 170 | - | - | - | - | - | - | |
| Average | Read | 400MB | chunk | | | 130 | 175 | 150 | 200 | 325 | 380 | 325 | 380 | 335 | 395 | |
| Current/Power | ricad | CHUIK | | | | 75 | 80 | 75 | 85 | 70 | 80 | 70 | 80 | 70 | 80 | |
| V00 2.2V | | | | | | 680 | 800 | 710 | 850 | 820 | 950 | 820 | 950 | 840 | 980 | |
| VCC = 3.3V VCCQ = 1.2V | | | | | | 130 | 135 | 135 | 140 | - | - | - | - | - | - | |
| VCCQ2= 1.8V | Write | 400MB cl | hunk | | | 60 | 95 | 75 | 110 | 220 | 280 | 220 | 280 | 230 | 300 | |
| Ta = RT | | | | | | 100 | 100 | 155 | 155 | 105 | 105 | 120 | 120 | 120 | 120 | |
| | | | | | | 600 | 670 | 810 | 880 | 750 | 860 | 800 | 900 | 810 | 940 | |
| Idle Current / Po | wer (Typic | cal), Recov | very=2ms | | | 42 | <u>20</u> .0 | 1 | 20 50 | 2, | - 40 | 24 | - | 20 | - : E | |
| | | | | | | | 0 | | 60 | | ±05 | 8 | | 10 | | |
| VCCQ2=1.8V, Ta | = RT | | | | | | 8 4 | | 12 | 0. | | 0. | | 1. | | |
| | | | | | | 42 | | | 20 | <u> </u> | , | <u> </u> | <i>, </i> | - | | |
| | | oical), Rec | overy=20ms | | | | 0 | † | <u> </u> | 23 | 30 | 23 | RN | 24 | 10 | |
| | | | | | | |)) | + | , 0 | |) | (| | ļ |) | |
| VCCQ2=1.8V, Ta | = RT | | | | | 0. | | 0. | | 0. | ~ | 0. | | 0. | | |
| | | | | TOWEI | [IIIIVV] | 0. | | indow | <i>J1</i> | 0. | ·- | 5us w | | 0. | 13 | |
| Peak Current (Ty | pical) | | | IccQ | [mA] | 305 | 320 | 295 | 310 | - | - | - | - | - | - | |
| VCC = 3.6V, VCC | | | | IccQ2 | [mA] | 180 | 215 | 205 | 240 | 400 | 450 | 400 | 450 | 400 | 450 | |
| VCCQ2 = 1.95V, Ta | = RT | | | Icc | [mA] | 315 | 325 | 465 | 465 | 350 | 360 | 400 | 400 | 480 | 500 | |
| | | | | | | | 5us w | indow | | | | 5us w | indow | | | |
| PeakCurrent Wo | rst (Worst) |) | | IccQ | [mA] | 405 | 420 | 400 | 410 | - | - | - | - | - | - | |
| VCC = 3.6V, VCCC | | | | IccQ2 | [mA] | 190 | 225 | 215 | 250 | 600 | 650 | 600 | 650 | 600 | 650 | |
| VCCQ2= 1.95V, Ta | = HT | | | Icc | [mA] | 370 | 373 | 530 | 550 | 450 | 460 | 500 | 500 | 560 | 570 | |

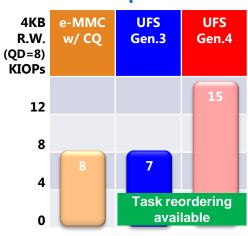
32GB e-MMC/UFS Performance/Power (incl. Target value) TOSHIBA

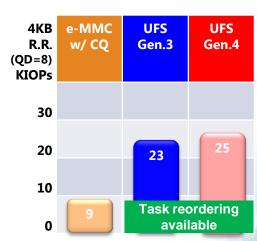




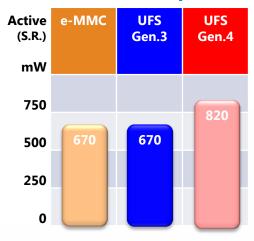
e-MMC Ver.5.1: HS400 mode UFS Ver.2.0 : HS-G3Bx1lane

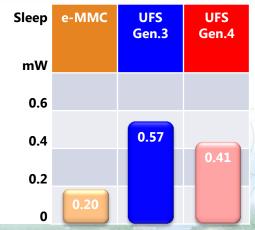
Random performance





Power consumption





This information is subject to change w/o notice.

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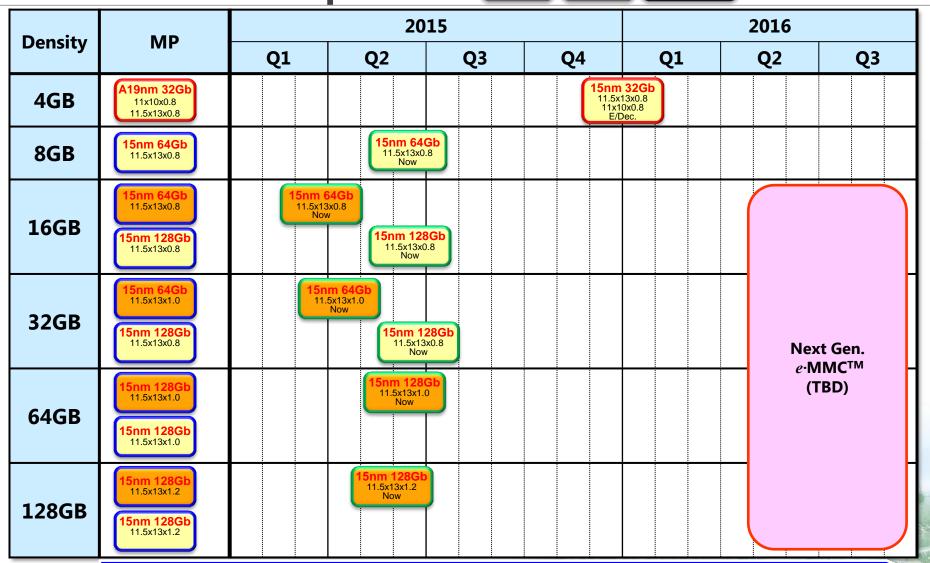


e·MMCTM Roadmap

 $e \cdot MMC^{TM}$ **Supreme**

 $e \cdot \mathsf{MMC^{TM}}$ **Premium** NAND Gen. Package Size CS Schedule

Seq.W [MB/s] M1CCL02-082 Oct., 2015 **TOSHIBA**



V5.1 V5.1 with CQ

Supreme+: Exclusively for 15nm 64GB (64Gb) device only 4GB: V5.0 devices

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